

Electronic and structural properties of grain boundaries in electron-irradiated edge-defined film-fed growth silicon

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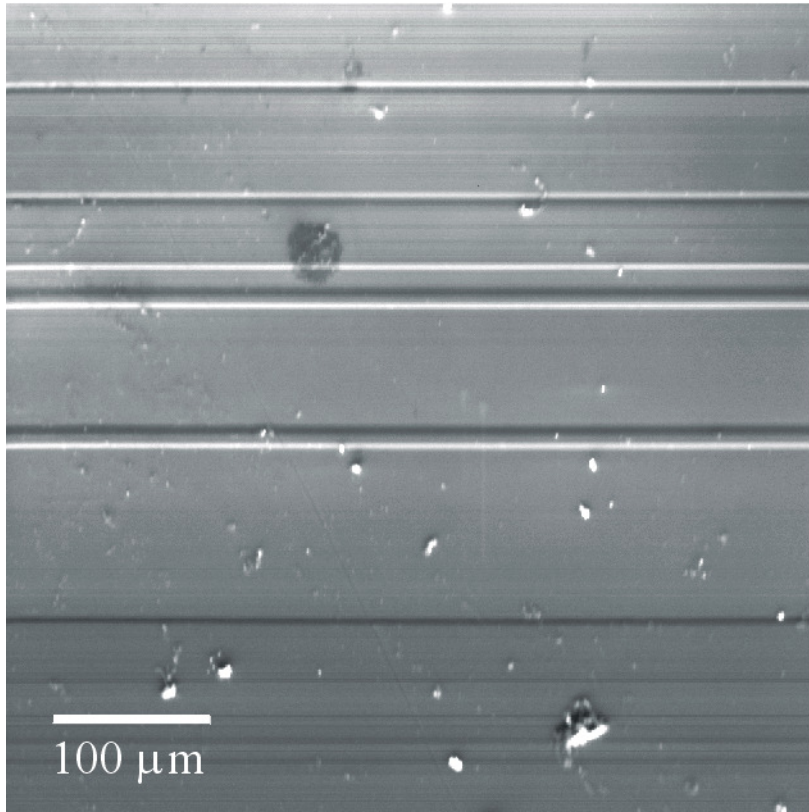


Fig.1

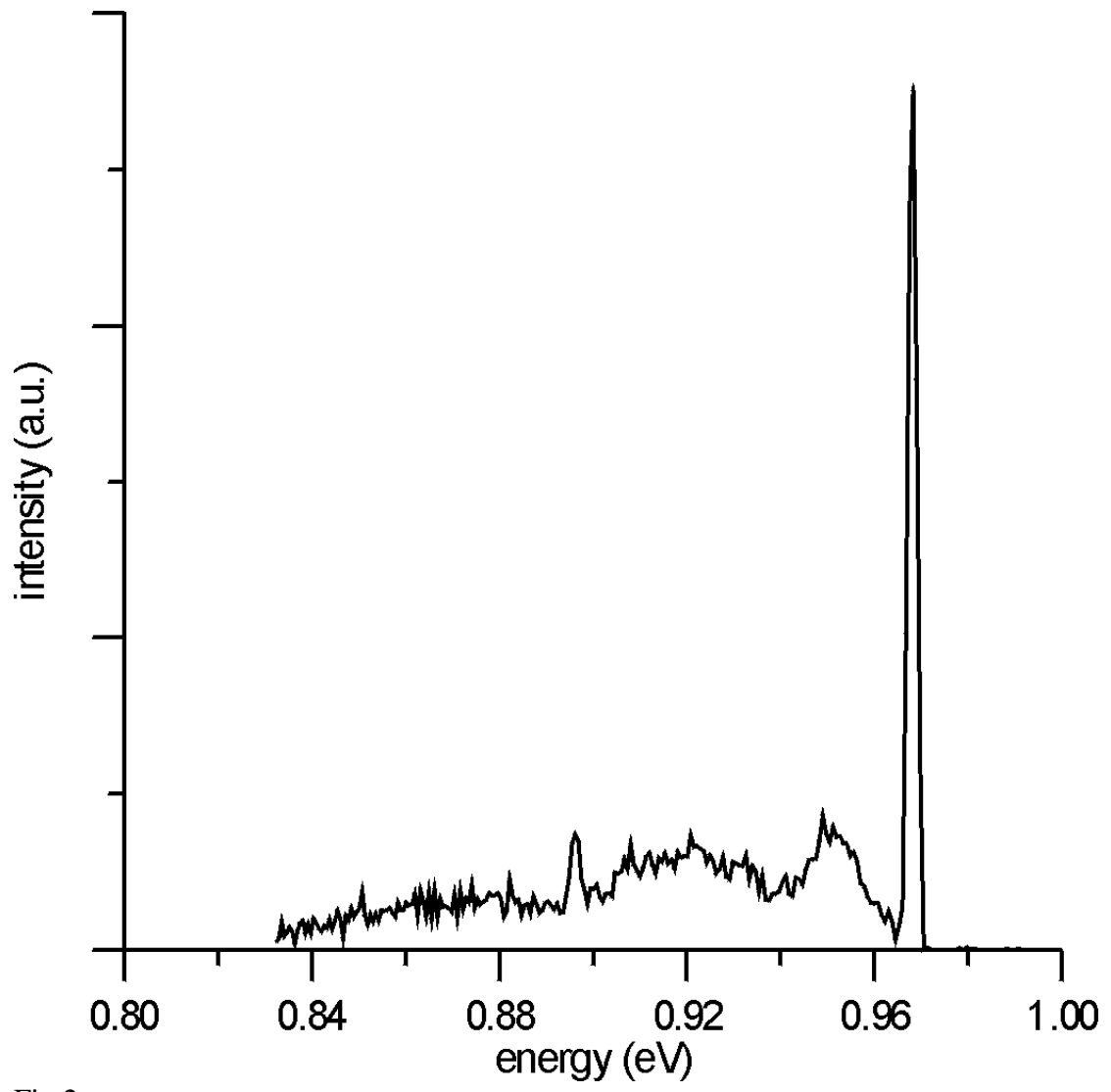


Fig 2

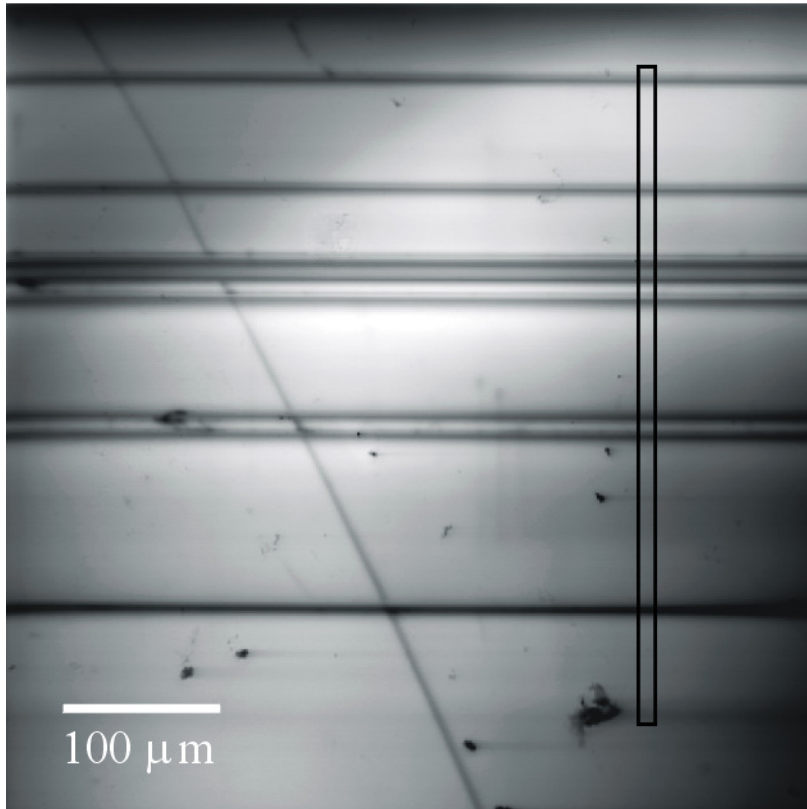


Fig 3(a)

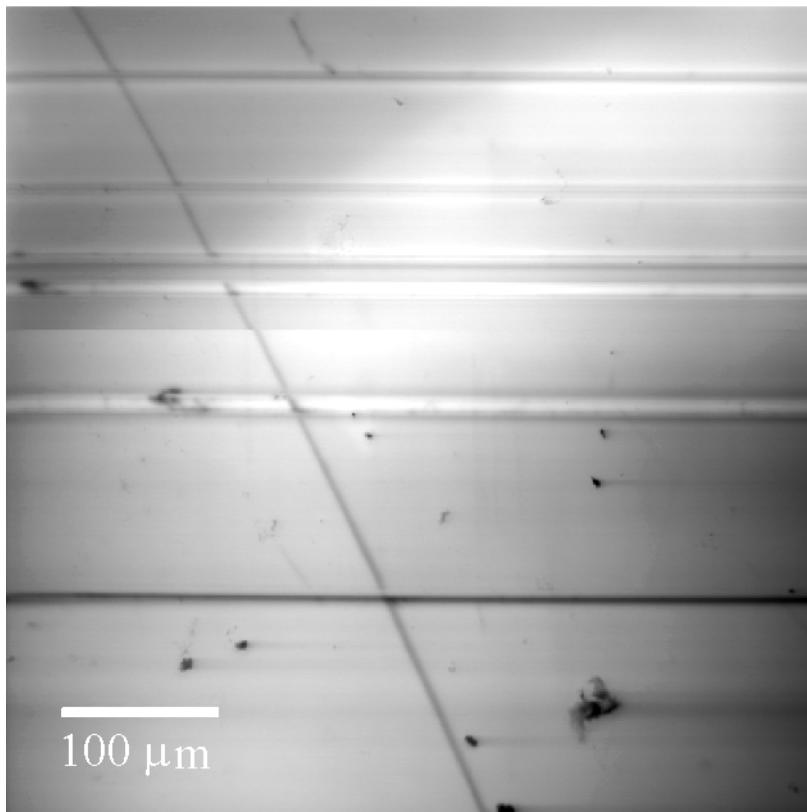


Fig 3(b)

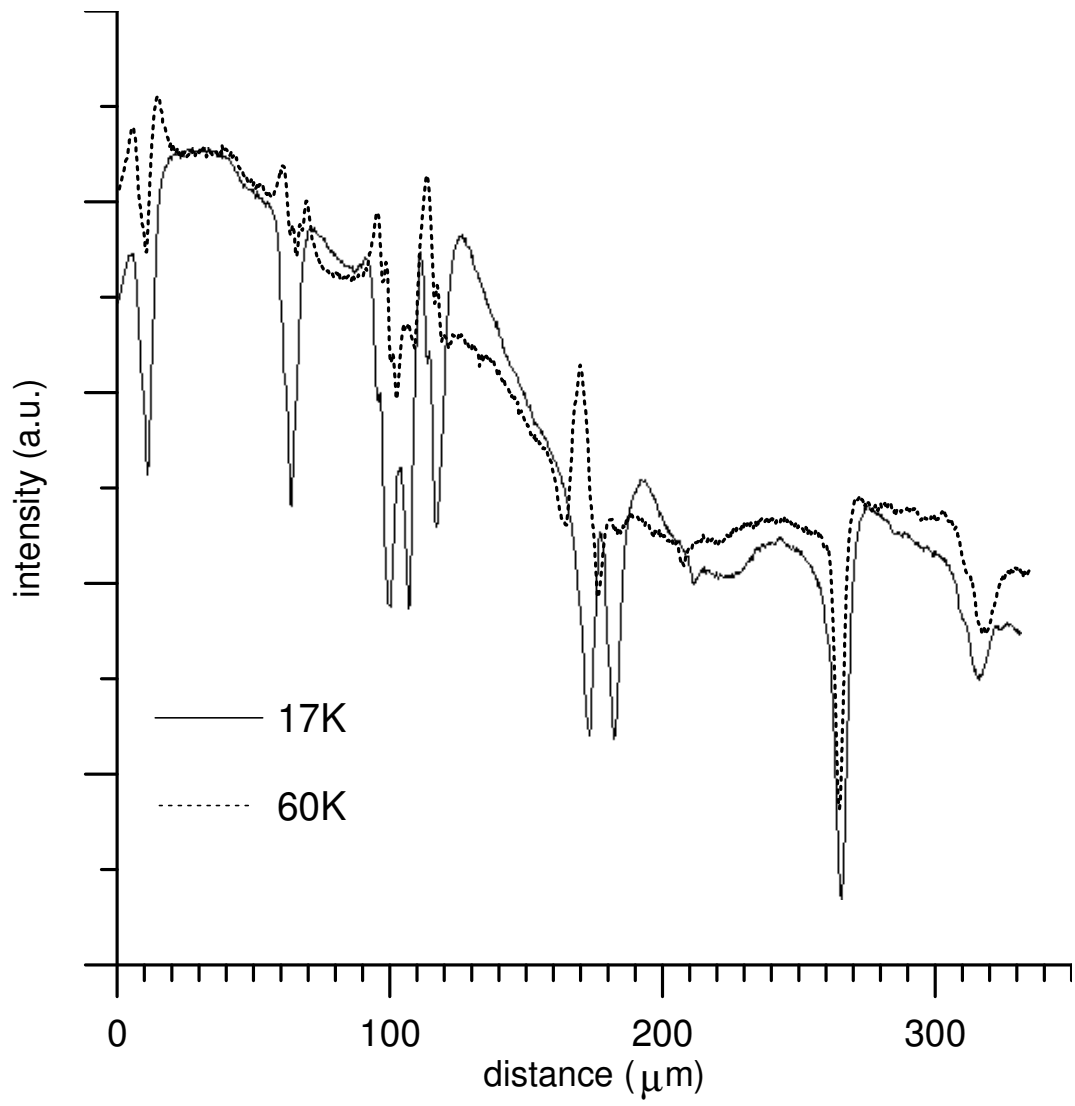


Fig 4

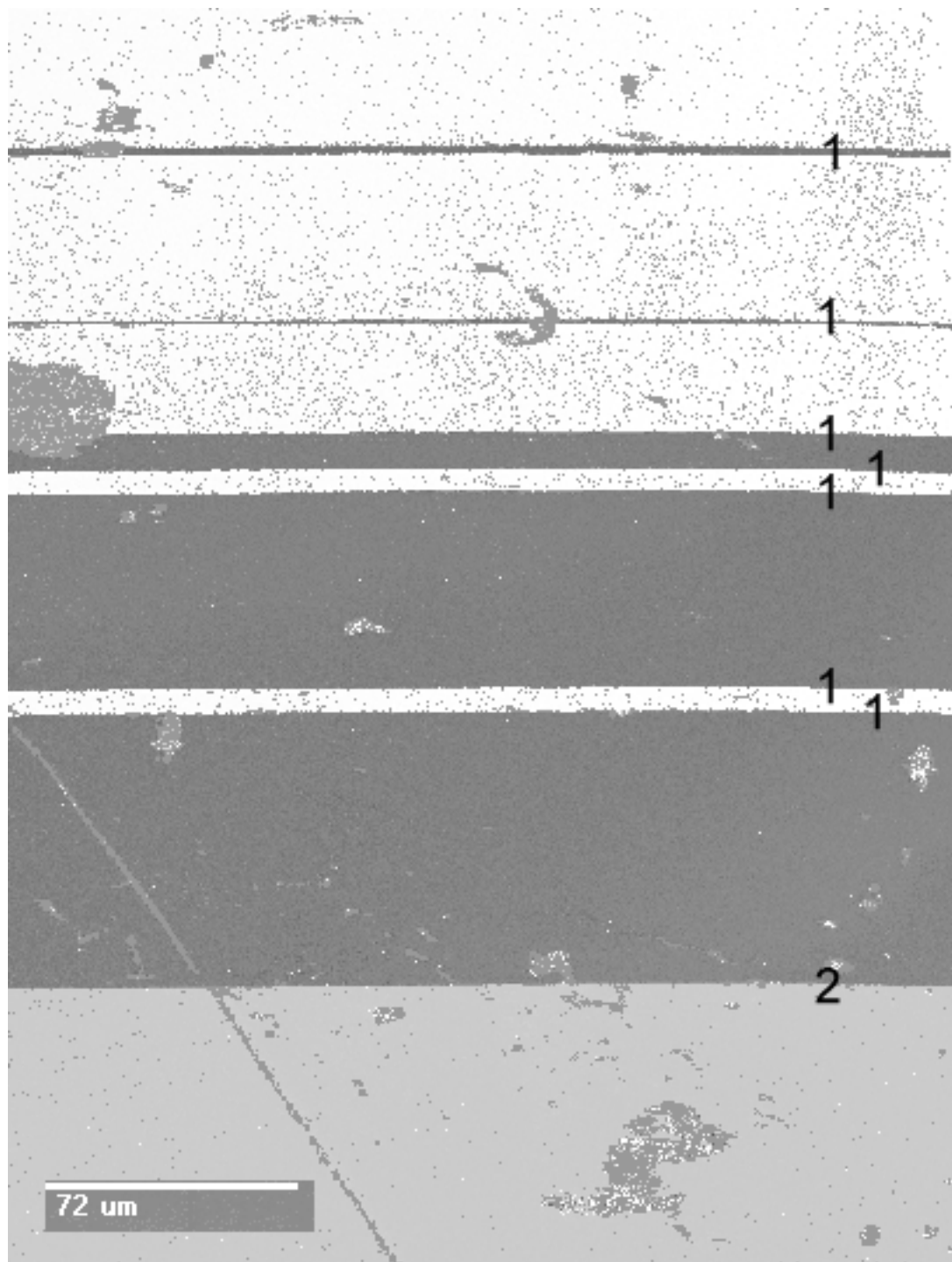


Fig 5